

## Silicon Super Fast Recovery Diode

$V_{RRM} = 50\text{ V} - 600\text{ V}$

$I_F = 100\text{ A}$

### Features

- High Surge Capability
- Types up to 600 V  $V_{RRM}$

D-67 Package



### Maximum ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

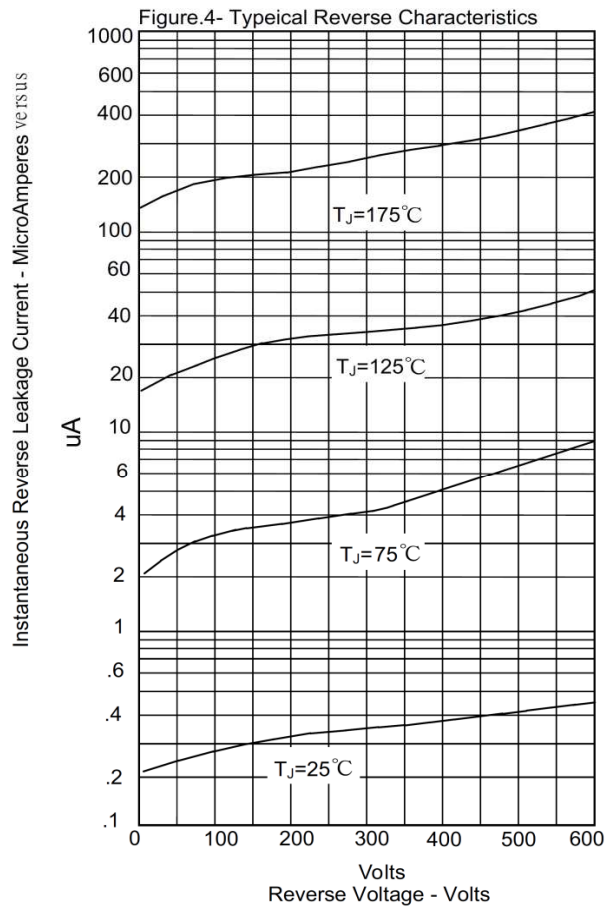
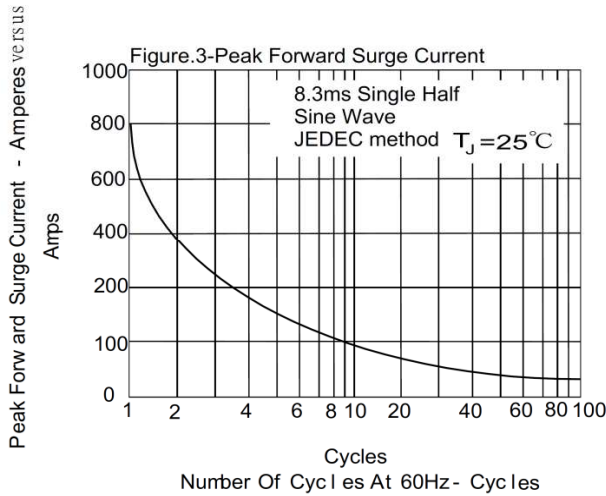
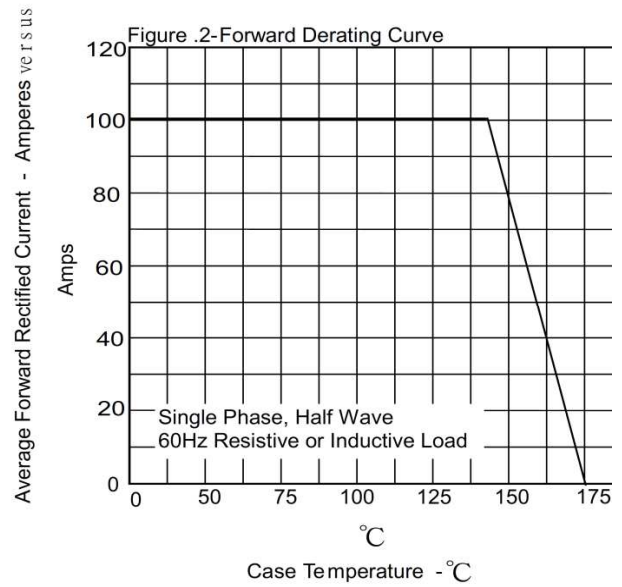
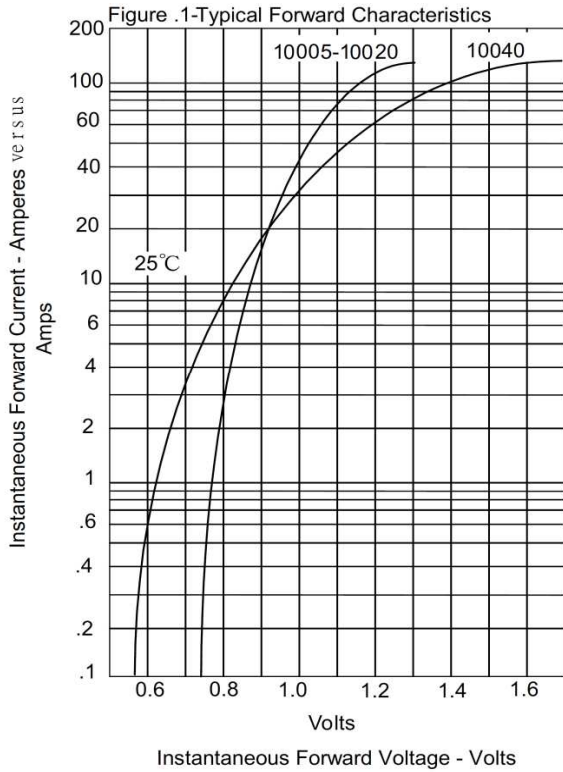
Parameter	Symbol	Conditions	MURH10005 (R)	MURH10010 (R)	MURH10020 (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		50	100	200	V
RMS reverse voltage	$V_{RMS}$		35	70	140	V
DC blocking voltage	$V_{DC}$		50	100	200	V
Continuous forward current	$I_F$	$T_C \leq 140\text{ °C}$	100	100	100	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	800	800	800	A
Operating temperature	$T_j$		-65 to 175	-65 to 175	-65 to 175	°C
Storage temperature	$T_{stg}$		-65 to 175	-65 to 175	-65 to 175	°C

### Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MURH10005 (R)	MURH10010 (R)	MURH10020 (R)	Unit
Diode forward voltage	$V_F$	$I_F = 100\text{ A}$ , $T_j = 25\text{ °C}$	1.3	1.3	1.3	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_j = 25\text{ °C}$	25	25	25	$\mu\text{A}$
		$V_R = 50\text{ V}$ , $T_j = 125\text{ °C}$	1	1	1	mA

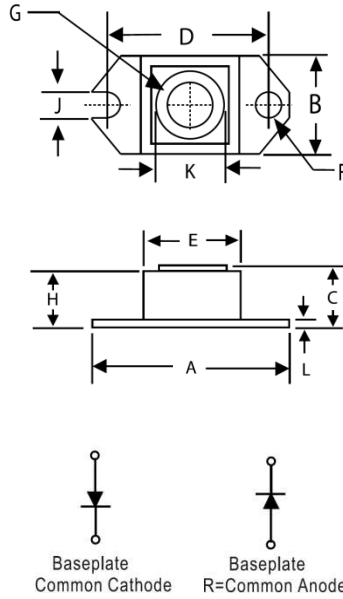
### Recovery Time

Maximum reverse recovery time	$T_{RR}$	$I_F = 0.5\text{ A}$ , $I_R = 1.0\text{ A}$ , $I_{RR} = 0.25\text{ A}$	75	75	75	nS
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## Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	1.515	1.560	38.48	39.62	
B	.725	.775	18.42	19.69	
C	.595	.625	15.11	15.88	
D	1.182	1.192	30.02	30.28	
E	.736	.744	18.70	18.90	
F	.152	.160	3.86	4.061	∅
G	1/4- 20 UNC				
H	.540	.580	13.72	14.73	
J	.156	.160	3.96	4.06	
K	.480	.492	12.20	12.50	∅
L	.120	.130	3.05	3.30	